

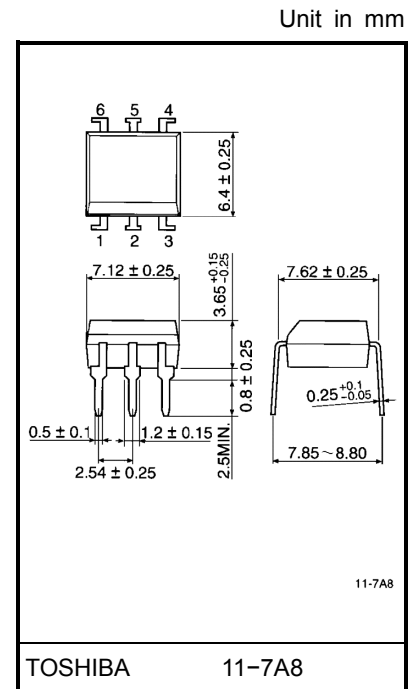
TOSHIBA Photocoupler GaAs IRed & Photo-Transistor

4N35(Short), 4N36(Short), 4N37(Short)

- AC Line / Digital Logic Isolator.
- Digital Logic / Digital Logic Isolator.
- Telephone Line Receiver.
- High Frequency Power Supply Feedback Control.
- Relay Contact Monitor.

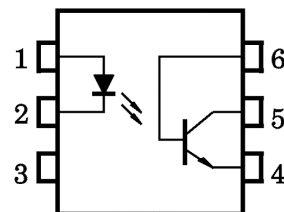
The TOSHIBA 4N35 (short) through 4N37 (short) consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor in a dual in-line package.

- Switching speeds: 3μs (typ.)
- DC current transfer ratio: 100% (min.)
- Isolation resistance: 10¹¹Ω (min.)
- Isolation voltage: 2500Vrms (min.)
- UL recognized: UL1577, file no. E67349



Weight: 0.4 g

Pin Configurations(top view)



- 1 : ANODE
- 2 : CATHODE
- 3 : N.C.
- 4 : EMITTER
- 5 : COLLECTOR
- 6 : BASE

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit							
LED	Forward current (continuous)	I_F	60	mA							
	Forward current derating	$\Delta I_F / ^\circ\text{C}$	0.8 (*)	mA / °C							
	Peak forward current (Note 1)	I_{PF}	3	A							
	Power dissipation	P_D	100	mW							
	Power dissipation derating	$\Delta P_D / ^\circ\text{C}$	1.33 (*)	mW / °C							
	Reverse voltage	V_R	6	V							
Detector	Collector-emitter voltage	BV_{CEO}	30	V							
	Collector-base voltage	BV_{CBO}	70	V							
	Emitter-collector voltage	BV_{ECO}	7	V							
	Collector current (continuous)	I_C	100	mA							
	Power dissipation	P_C	300	mW							
	Power dissipation derating	$\Delta P_C / ^\circ\text{C}$	4.0 (*)	mW / °C							
Coupled	Storage temperature	T_{stg}	-55~150	°C							
	Operating temperature	T_{opr}	-55~100	°C							
	Lead soldering temperature (at 10 s)	T_{sol}	260	°C							
	Total package power dissipation	P_T	300	mW							
	Total package power dissipation derating	$\Delta P_T / ^\circ\text{C}$	3.3 (*)	mW / °C							
		BV_S	2500	V _{rms}							
	Input to output isolation voltage (AC, 1 minute)	<table border="1"> <tr> <td>4N35</td> <td rowspan="3">$BV_S (**)$</td> <td>2500 / 3550</td> <td rowspan="3">V_{rms} / V_{pk}</td> </tr> <tr> <td>4N36</td> <td>1750 / 2500</td> </tr> <tr> <td>4N37</td> <td>1050 / 1500</td> </tr> </table>	4N35	$BV_S (**)$	2500 / 3550	V _{rms} / V _{pk}	4N36	1750 / 2500	4N37	1050 / 1500	
4N35	$BV_S (**)$	2500 / 3550	V _{rms} / V _{pk}								
4N36		1750 / 2500									
4N37		1050 / 1500									

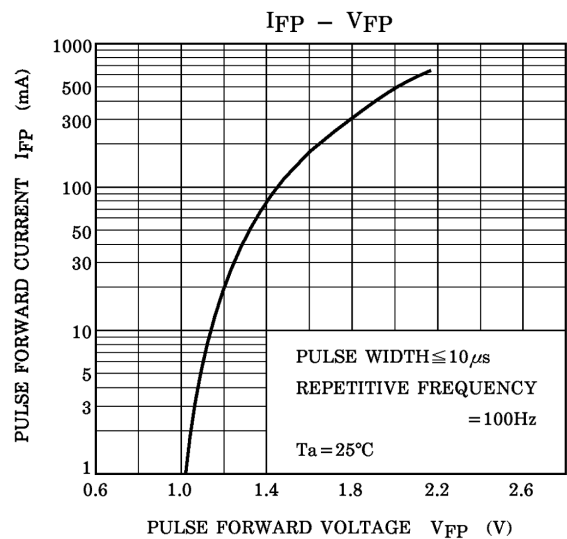
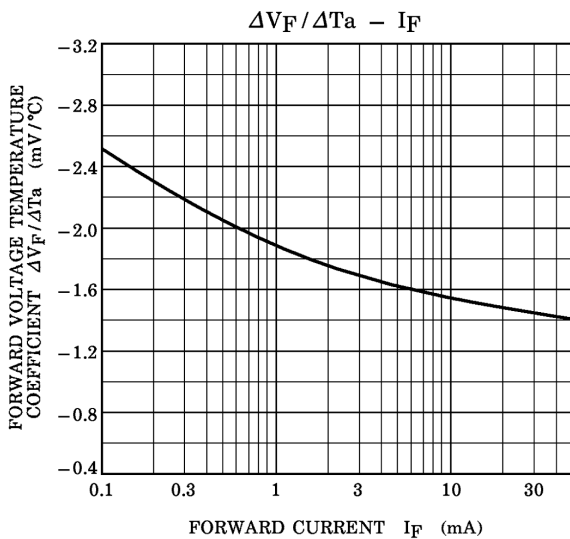
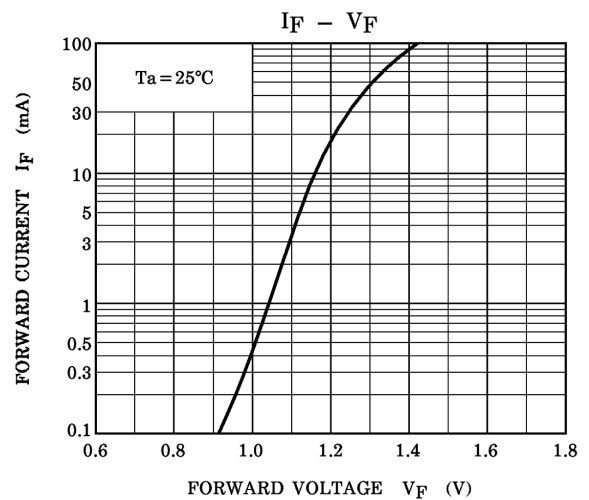
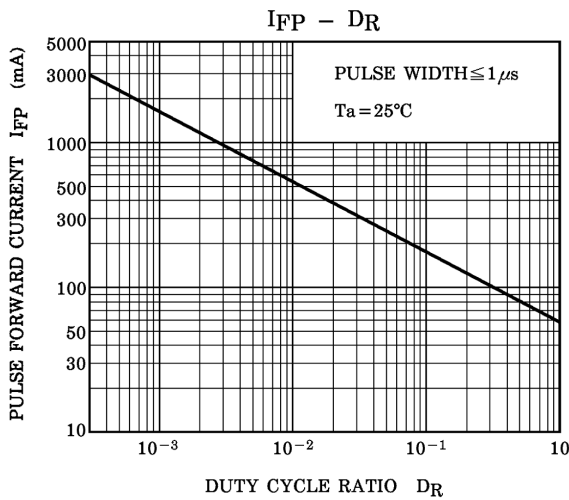
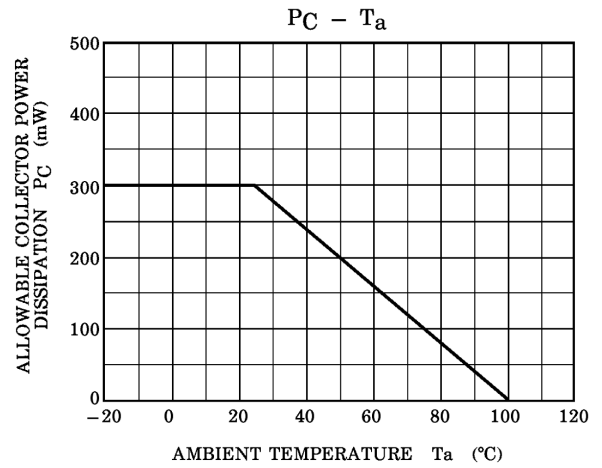
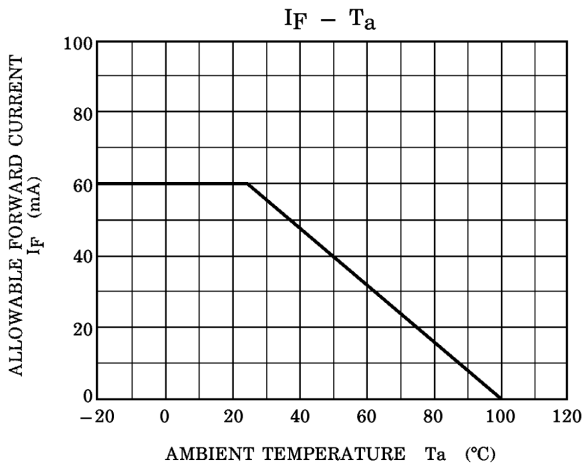
(Note 1) Pulse width 1μs, 300pps

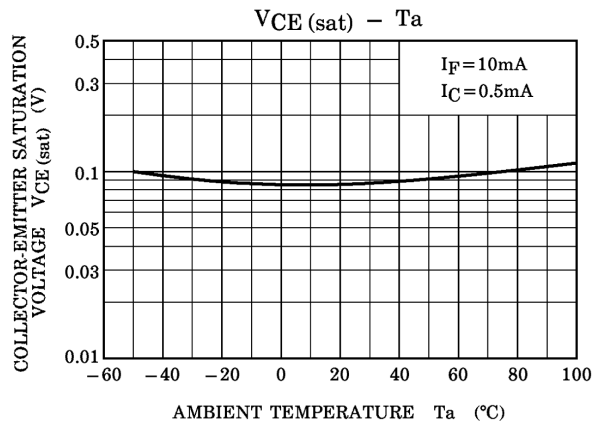
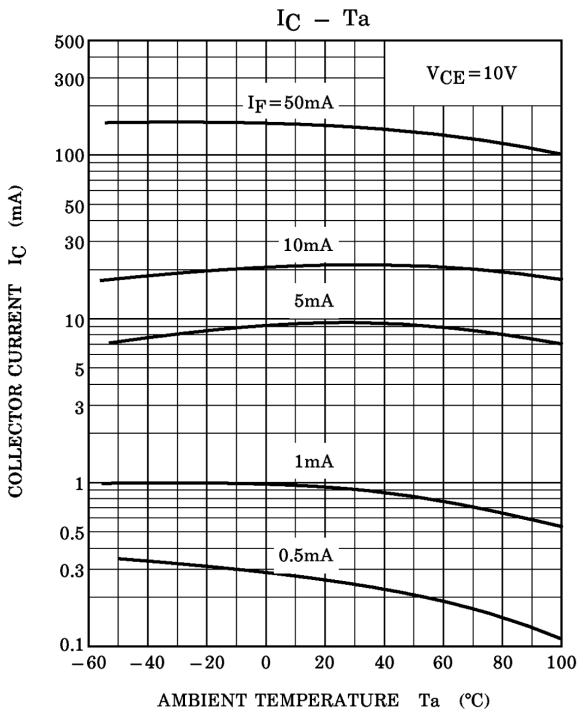
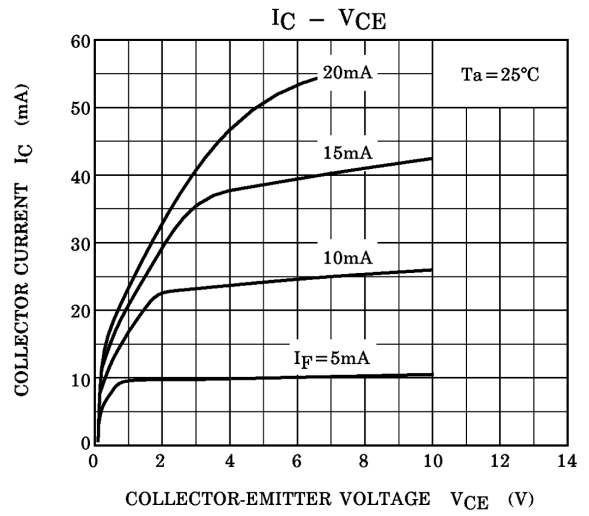
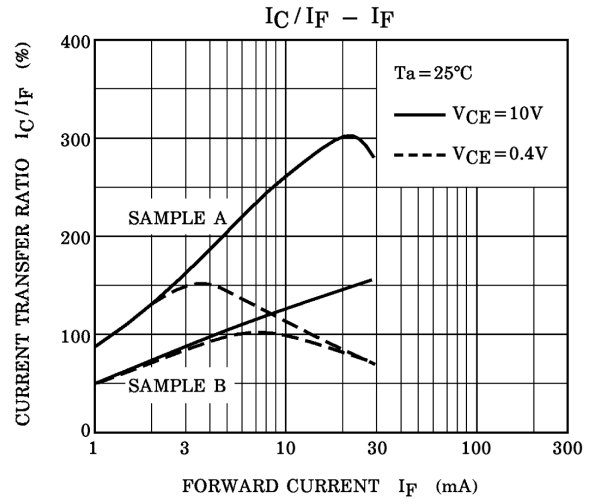
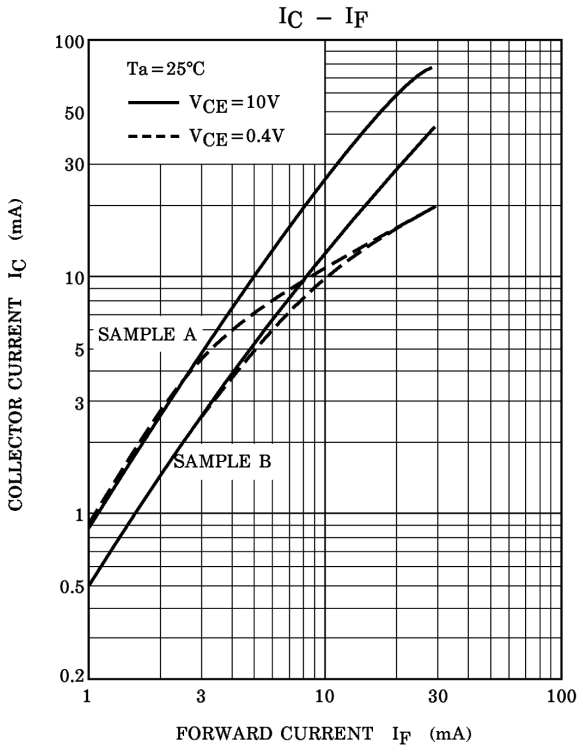
(*) Above 25°C ambient.

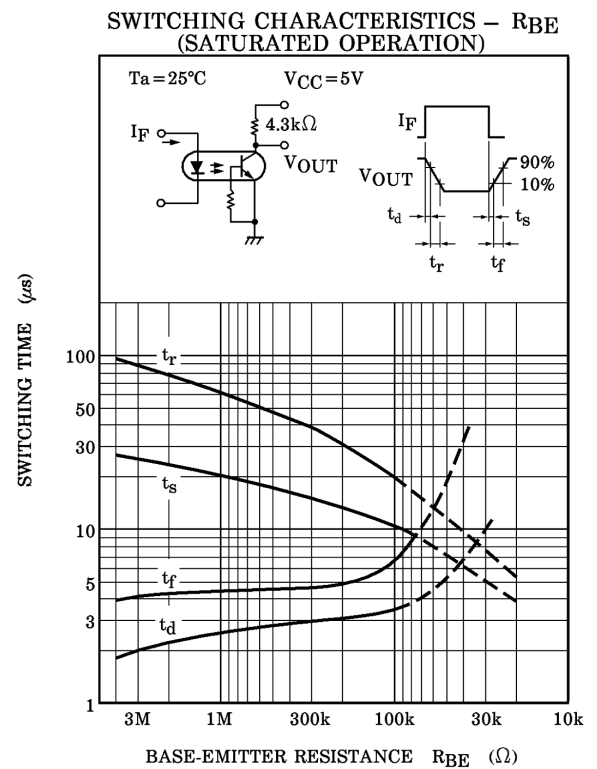
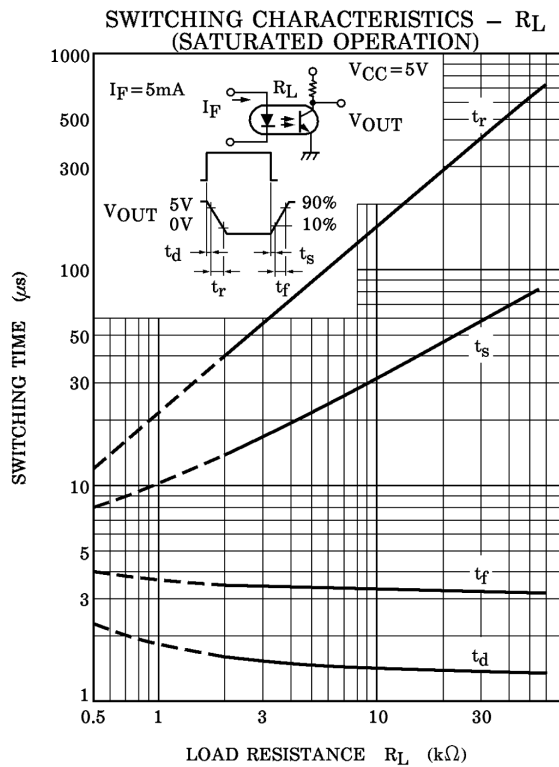
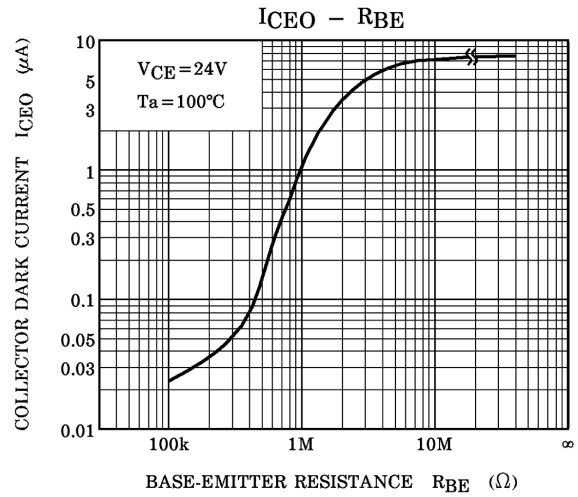
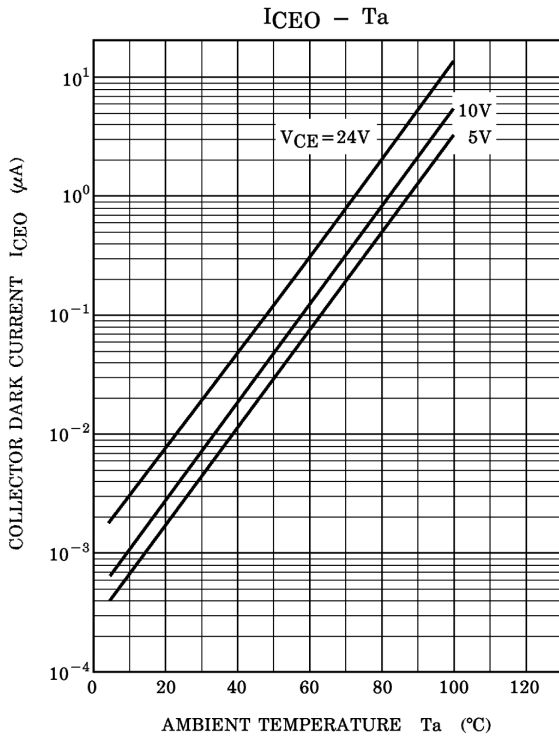
(**) JEDEC registered maximum BV_S , however, TOSHIBA specifies a maximum BV_S of 2500V_{rms}, 1 minute.

Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit	
LED	Forward voltage	V_F	$I_F = 10 \text{ mA}$	0.8	1.15	1.5	V	
			$I_F = 10 \text{ mA}, T_a = -55^\circ\text{C}$	0.9	—	1.7		
			$I_F = 10 \text{ mA}, T_a = 100^\circ\text{C}$	0.7	—	1.4		
Reverse current		I_R	$V_R = 6 \text{ V}$	—	—	10	μA	
Capacitance		C_D	$V = 0, f = 1 \text{ MHz}$	—	30	100	pF	
Detector	DC forward current gain		h_{FE}	$V_{CE} = 5 \text{ V}, I_C = 500 \mu\text{A}$	—	200	—	—
	Collector-emitter breakdown voltage		$V_{(BR)CEO}$	$I_C = 10 \text{ mA}$	30	—	—	V
	Collector-base breakdown voltage		$V_{(BR)CBO}$	$I_C = 100 \mu\text{A}$	70	—	—	V
	Emitter-collector breakdown voltage		$V_{(BR)ECO}$	$I_E = 100 \mu\text{A}$	7	—	—	V
	Collector dark current		I_{CEO}	$V_{CE} = 10 \text{ V}$	—	1	50	nA
	Collector dark current		I_{CEO}	$V_{CE} = 30 \text{ V}, T_a = 100^\circ\text{C}$	—	—	500	μA
	Collector-emitter capacitance		C_{CE}	$V = 0, f = 1 \text{ MHz}$	—	10	—	pF
Coupled	Current transfer ratio	I_C / I_F	$I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	100	—	—	%	
			$I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V}, T_a = -55^\circ\text{C}$	40	—	—		
			$I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V}, T_a = 100^\circ\text{C}$	40	—	—		
	Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_F = 10 \text{ mA}, I_C = 0.5 \text{ mA}$	—	0.1	0.3	V
	Capacitance input to output		C_S	$V_S = 0, f = 1 \text{ MHz}$	—	0.8	2.5	pF
	Isolation resistance		R_S	$V_S = 500 \text{ V}, R.H. \leq 60 \%$	10^{11}	—	—	Ω
	Input to output isolation current (pulse width = 8ms)	4N35	I_{IO}	$V_{IO} = 3550 \text{ Vpk}$	—	—	100	μA
		4N36		$V_{IO} = 2500 \text{ Vpk}$	—	—	100	
		4N37		$V_{IO} = 1500 \text{ Vpk}$	—	—	100	
Turn-on time		t_{ON}	$V_{CC} = 10 \text{ V}, I_C = 2 \text{ mA}, R_L = 100\Omega$	—	3	10	μs	
Turn-off time		t_{OFF}		—	3	10		







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